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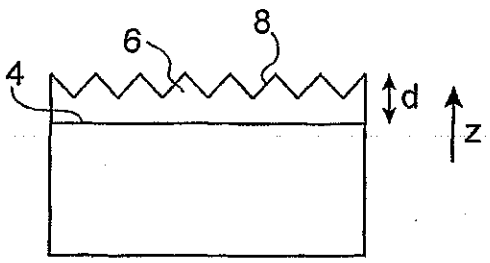
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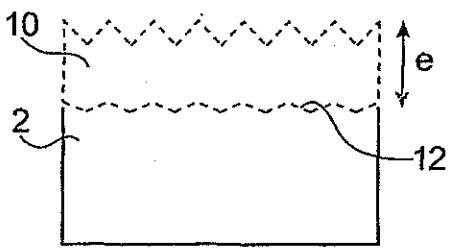
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(54) Title: SURFACE ROUGHENING PROCESS



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(57) Abstract: The invention relates to a process of forming a rough interface (12) in a semiconductor substrate (2), comprising: the formation, on a surface (4) of said substrate, of a zone of irregularities (8) in or on an oxide or a material (6) that may be oxidized, the formation of roughnesses in or on the semiconductor substrate (2) by thermal oxidation of or through this material or this oxide (6) and a part of the semiconductor substrate.

WO 2008/090428 A1